Coherent single electron spin control in a slanting Zeem an eld

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We consider a single electron in a 1D quantum dot with a static slanting Zeem an eld. By combining the spin and orbital degrees of freedom of the electron, an elective quantum two-level (qubit) system is defined. This pseudo-spin can be coherently manipulated by the voltage applied to the gate electrodes, without the need for an external time-dependent magnetic eld or spin-orbit coupling. Single qubit rotations and the C-NOT operation can be realized. We estimated relaxation (T_1) and coherence (T_2) times, and the (tunable) quality factor. This scheme implies important experimental advantages for single electron spin control.

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Stimulated by electron-spin-based proposals for quantum computation [1], a growing interest has emerged in realizing the coherent manipulation of a single electron spin in a solid-state environment. The application of the electron's spin { rather than its charge { as a quantum bit (qubit) is motivated by its potentially long coherence time in solids and the fact that it comprises a natural two-level system. Single electron spin resonance (SESR) plays a key role in realizing electron-spin-qubit rotation. Im portantly, SESR is also the prime tool for determ ining the single electron spin coherence time T2 in con ned solid-state systems such as quantum dots (QDs). The induced Rabioscillations can be read out via electron transport [2] or optically [3], giving an estimate for T_2 . SESR was detected in param agnetic defects in silicon [4] and for nitrogen vacancies in diam ond [5], but not in sem iconductorQDs so far. Realizing SESR in QDs is hard, not least because of the necessary high-frequency (10 GHz) m agnetic eld in a cryogenic (100 m K) setup. W aveguides and microwave cavities as used in conventional ESR [6], cause serious heating, lim iting the operation tem perature 1 K .O n-going work in our group focuses on generating ac magnetic elds by an on-chip microscopic coil [7].

In this Letter, we propose a new SESR scheme that elim inates the need for an externally applied ac magnetic eld, and with the potential of very high and tunable quality factors. An ac voltage is applied to let an electron in a Q D oscillate under a static slanting Zeem an eld. This e ectively provides the electron spin with the necessary time-dependent magneticeld. Note the analogy with the Stem-Gerlach experiment, where the spin and orbital degrees of freedom are coupled by employing an inhomogenous magnetic eld. The spatial oscillation of the electron within the QD involves the hybridization of orbital states, as schem atically depicted in Fig: 1a for the case of the two lowest orbital states, n = 1;2. Charge qubits based on double QDs [8] o er great tunability, but su er from short coherence times (1 ns) [9]. Spin qubits on the contrary, enable long coherence

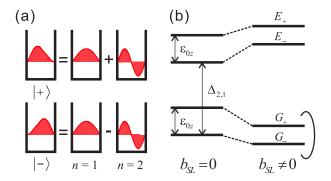


FIG.1: (a) Schem atic representation of how a spatial oscillation between wavefunctions j+i and j i involves hybridization ofmultiple orbital states. (b) Energy spectrum of a quantum dot (QD) with two orbital levels (level spacing $_{2;1}$) and constant Zeem an energy $"_{0z}$ with/without a magnetic eld gradient $b_{\rm SL}$. The lowest levels, jG i, constitute a qubit. \pm i are excited states.

times (1 s) [10], but are much harder to control, as pointed out above. Here, we present a hybrid charge-spin system that is promising both in terms of tunability and coherence. A nalogously, the combination of the ux and charge degrees of freedom has proved to be fruitful in superconducting qubits [11]. We stress that in our system spin-orbit (SO) coupling is not required, as opposed to earlier work on electron spin control based on g-tensor modulation [12], and on electric elds [13].

A possible realization of the system is presented in Fig: 2. A 1D conductor like a carbon nanotube or sem iconductor nanow ire is gated by ferrom agnetic electrodes that de ne both the tunnel barriers of the QD and the slanting magnetic eld. A Itematively, the slanting Zeem an eld could be provided by a static inhom ogeneity in the nuclear spin polarization or in the g-factor. The total magnetic eld is given by $B = b_{\rm SL} z i_{\rm x} + (B_0 + b_{\rm SL} x) i_{\rm z}$, where B_0 is the external uniform magnetic eld paral-

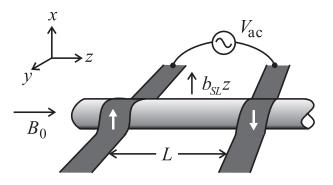


FIG. 2: Model of the 1D QD in a slanting Zeem an eld. Ferrom agnetic gate electrodes (dark grey) are located at either end of the dot and are magnetically polarized in the plus/m inus x-direction, creating a magnetic eld gradient $b_{S\,L}$. A uniform magnetic eld B $_0$ is applied in the z-direction. The spin in the dot is controlled by applying an oscillating voltage Vac between the two gates.

lel to the z-axis and bs is the z-direction gradient of the eld parallel to the x-axis (the middle of the QD corresponds to z = 0.). A true 1D system is assumed with an electron strongly con ned in the x and y directions. Therefore, the inhom ogeneous term along the z axis, b_{SL} xiz, can be eliminated (which is there to let B obey M axwell's equations).

The Hamiltonian is $H_0 = H_{00} + H_{0s}$, where $H_{00} =$ $\frac{p_z^2}{2m}$ + V (z) $g_B B_0 S_z$, and $H_{0s} = g_B b_{SL} z S_x$, with S = $\frac{1}{2}$, the Pauli spin matrices, g the e ective gfactor, and $_{\rm B}$ the Bohr magneton [14]. V (z) is the con nem ent potential of the QD with length L. The eigenvalues of H $_{00}$ are $\mathbf{n}_{n} = \mathbf{n}_{n} + \frac{1}{2}\mathbf{n}_{0z}$, and the eigenfunctions hzj; i = n(z), where n = 1; 2; ..., = 1 is the spinor. We de ne the Zeem an energy $"_{0z} = \dot{q}_{B} B_{0} \dot{j}$, which is assumed to be smaller than the orbitalenergy levelseparation $n_m = n_m = n_m$ U the charging energy. The non-zero matrix elements of $\#_{0s}$ in; i $\frac{1}{2}$ M m ; n, with a coupling energy M $_{\text{m}}$; $_{\text{n}}$ E $_{\text{SL}}$ $_{\text{m}}$; $_{\text{n}}$ where E $_{\text{SL}}$ $_{\text{SL}}$ b $_{\text{SL}}$ L characterizing the strength of the slanting eld, and the form dz m (z) $\frac{z}{L}$ n (z). factor m;n

By requiring the con ning potential to have a mirror sym m etry, ix: V(z) = V(z), the diagonal coupling energy elements vanish, namely $M_{n;n} = 0$. We employ perturbation theory up to the second order in E_{SL} and obtain the ground-state energy for a pseudo- $_{\rm n>0}$ C $_{\rm n}^{(2)}$ ½n + 1; i [15]. Since we assum ed $_{\rm 2;1}$ > $\rm "_{\rm 0z}$, the two lowest energy states 15+i and 15 i represent an energetically isolated qubit (see Fig: 1). We can disregard higher energy states, such as E i. For a rectangular con ning potential, we nd for the form factor $_{2n+1;21} = \frac{8}{2} (1)^{1+n} \frac{21(1+2n)}{((1+2n)^2 + 41^2)^2}$, while for a harmonic potential V (z) = $\frac{m!_0^2}{2}$ z², we have 2n+1;21 =

 $q = \frac{q}{n+1;1} + \frac{p}{n+\frac{1}{2}} + \frac{p}{n;1} = \frac{q}{m!_0}.$ Therefore, nm is negligible for large jn m j, and we only consider M 1;2 and M 2;3, which is exact for the harmonic potential. We de ne the e ective Zeem an energy "oz [1

We consider the qubit rotation induced by an acelectric eld. The time-dependent perturbation $H_1(t) =$ eV_{ac} (t) $\frac{z}{L}$ is applied to the system by introducing an oscillating signal V_{ac} (t) = $V_0 f$ (t) to the gate electrodes, as shown in Fig: 2. Since H 1 (t) is an odd function of z and is independent of spin, only the o -diagonal matrix elements of H₁ remain, hG H₁G i C₁⁽¹⁾)eV (t) ₂₁ $\frac{1}{2}$ "xf (t); and the diagonal elements are zero for any order. Therefore, the e ective Ham iltonian of our qubit is H $_{\rm e}$ = $\frac{1}{2}$ " $_{\rm z}$ $_{\rm z}$ + $\frac{1}{2}$ " $_{\rm x}$ f (t) $_{\rm x}$; which is form ally equivalent to the conventional ESR Hamiltonian [16]. For a sinusoidal perturbation $f(t) = \cos t$ at resonance ($\sim ! = "_z$), the time required for the -operation, i.e. jG_+ i! jG i, is given by

$$t = \frac{2 \sim \frac{2 \sim 2;1}{12}}{\frac{2}{12} eV_0 E_{SL} j} (1 - \frac{\frac{10}{0z}}{\frac{2}{2};1}):$$
 (1)

Since we hybridize the spin and orbital degrees of freedom, orbital relaxation processes harm the spin coherence. We not that acoustic phonon scattering is the dom inant relaxation m echanism for the energies relevant in our system. The electron-phonon scattering Ham iltonian is

$$H_{e ph} = X_{q (e^{iqz}b_{q}^{y} + H \mathcal{L};)}$$

$$= X_{q (x_{q} + x_{q}^{z})b_{q}^{y} + H \mathcal{L};}$$

$$= \frac{1}{2}g_{B}(B_{x}(t)_{x} + B_{z}(t)_{z});$$
(3)

where q is the phonon wave number, q is the coupling constant and b_{α}^{y} is the phonon creation operator. In Eq. 2, we project H_{e ph} to the qubit base, where the effective coupling constants are ${}^x_q = {}_q h l \, \dot{e}^{iqz} \, 2 i (C_{1;+}^{(1)} + C_{1;}^{(1)})$ and ${}^z_q = {}_q h l \, \dot{e}^{iqz} \, \beta i (C_{1;+}^{(2)}) \cdot B_r \, (t) \, (r = 1)$ x;y;z) represents the uctuating magnetic eld caused by phonons. A standard Bom-Markov approximation [16] gives relaxation (T_1) and coherence (T_2) times as follows,

$$T_1^{-1} = k_{xx} ("_z) + k_{yy} ("_z);$$
 (4)

$$T_1^{1} = k_{xx} ("_z) + k_{yy} ("_z);$$
 (4)
 $T_{2phonon}^{1} = (2T_1)^{1} + k_{zz} (0);$ (5)

where k_{rr^0} (~!) $\frac{1}{2}$ (g B) $\frac{1}{2}$ d $\cos(!)$ hB_r (t)B_{r0} (t+)i₀ with h oreginesenting the thermal average. The dephasing term k_{zz} (0) related to B $_z$ (t) $_z$ is negligible since 1 and is shown to be absent in the zero frequency lim it. This situation is similar to that of a spin qubit with SO interaction [17, 18]. The relaxation rate $\rm T_1^{-1}$ is then

w ith ~! $_q$ the phonon energy, = 1=(k_B T), and the relaxation time $_p$ (E) de ned in analogy w ith Ferm i's G olden rule for a transition from level 2 to 1 w ith energy transfer E. The coherence time is obtained by

$$T_{2\text{total}}^{1} = T_{2\text{phonon}}^{1} + T_{2\text{spin}}^{1};$$
 (7)

where we included the generic spin coherence time $T_{2\rm spin}$, which is the 'pure' coherence time of the electron spin in the QD. The upper bound of the quality factor of the one-qubit operation is characterized by $2T_1$ divided by tofEq: (1),

$$Q = \frac{2 \cdot 2; 1 \cdot p \cdot (\mathbf{v}_z)}{\sim} \frac{eV_0}{\mathcal{F}_{SL} j} (1 - \frac{\mathbf{v}_{0z}^2}{2});$$
 (8)

Im portantly, the quality factor is tunable by controlling the am plitude of the ac voltage m odulation, V_0 .

For the practical im plem entation of our scheme, 1D systems with small electron-phonon coupling and/or weak SO coupling are favorable. Single wall carbon nanotube QDs are very suitable, because of the absence of piezoelectricity and the weak deform ation potential coupling [19]. SO coupling does not play a role either. QDs in sem iconductor (e.g.: SiG e) nanow ires are also good candidates, since 1D phonons couple weakly to the electron orbitals. Here we estimate T_1 and Q of GaAs1DQDsembedded in bulk AlGaAs. Since the phonon character is 3D in this system, the results are worse than for the more suitable systems given above. Figure 3a shows the low-tem perature ($"_z$ 1) relaxation rate caused by bulk acoustic phonons in a QD with longitudinal parabolic con nem ent $\sim !_0 = 1 \text{ m eV}$ and a transversal con nem ent of 10 m eV. $E_{SL} = 1$ eV, corresponding to $b_{SL} = 1:16 \text{ T/m}$, which can be realized with a ferrom agnetic m aterial [20]. Of the three acoustic phonon scattering m echanism s, transversal piezoelectric scattering is dominant for low B_0 , where T_1 is of the order of 10 ms. For comparison, the typical relaxation time from higher levels, i.e. £ i! 16 i in Fig: 1b is much shorter, 10 ns, dom inated by the deform ation potential scattering. Note that the contribution of SO interaction (D resselhaus coupling) is very sm all (T_{2SO} QDs, in contrast to disk-shaped dots as exam ined in Ref: [17]. Figure 3b shows Q for various con nement potentials (dot length L) with $b_{SL} = 1:16 \text{ T/m} \cdot V_0 = 10 \text{ V}$ [21, 22], and t 400 ns for $\sim !_0 = 1 \text{ m eV}$. A quality factor Q & 10^4 is often used as a threshold for viable quantum computation [23].

W e study the time evolution of the density matrix of the four levels $f\!\!G$ i; $f\!\!E$ i, including V_{ac} (t) and phonon

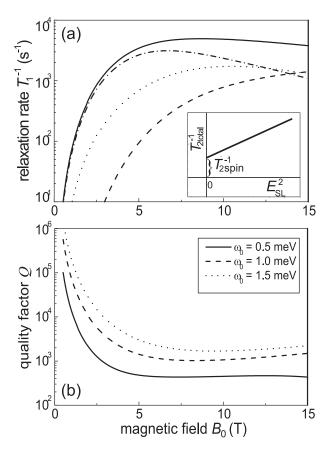


FIG. 3: (a) Relaxation rate T_1^{-1} in a 1D GaAs QD as function of external magnetic eld B $_0$ due to dierent phonon scattering mechanisms: deformation potential (dashed), longitudinal piezoelectric (dotted), transversal piezoelectric (dash-dotted). The solid line is the total scattering rate. Inset: schematic derivation of the pure electron spin coherence time $T_{\rm 2spin}$ from the dependence of the total coherence time $T_{\rm 2total}$ on the strength of the slanting eld $E_{\rm SL}$. (b) B_0 -dependence of the quality factor Q for a single qubit operation.

scattering. Near the resonant condition $\sim ! = "_z, \pm i$ are almost empty and do not contribute to the qubit dynam ics at all. T_{2total} can be evaluated using a timeresolved measurement of the Rabi oscillation (see e.g. [2]). After rotating the qubit over a certain angle, a projection measurement is done into G i or G i using a single-shot read out scheme based on spin-to-charge conversion [24]. Both energy selectivity and spin selectivity of tunneling out of the QD are applicable for our pseudo-spin qubit system. The read-out error introduced by level m ixing to n = 2 by the slanting eld is negligible, namely of the order $(C_1^{(1)})^2$ 10 6. Im portantly, the pure electron spin coherence time T_{2spin} can be evaluated by extrapolating the $T_{\text{2total}}\text{--}\text{dependence}$ on E $_{\text{SL}}$ where $T_{2phonon}^{-1}$ / E_{SL}^{2} (see Eq. (6)), as shown in the inset to Fig: 3a.

For a universal set of quantum gates a two-qubit gate is required. Here we present a realization of a two-qubit

gate based on two coupled dots in series [8]. A lthough it has been pointed out that an inhom ogeneous magnetic eld introduces swap errors [25, 26], we show that correct swap operation is possible in our system . The two-qubit H am iltonian is H = $_{\rm i=L\,;R}$ H $_{\rm 0\,i}$ + H $_{\rm T}$ + H $_{\rm V}$; where H $_{\rm 0\,i}$ is the single-dot H am iltonian i = L;R (ac eld is o , "_x = 0), H $_{\rm T}$ represents the tunneling between the dots, and H $_{\rm V}$ represents the inter-dot interaction V . By projecting the H am iltonian onto the qubits, we nd

$$H_{0i} = \frac{\mathbf{v}_{z}}{2} X$$
 $c_{i}^{y} c_{i} + U n_{i} n_{i};$ (9)

$$H_{T} = {X \atop [t \ c_{L}^{y} \ c_{R} \ + s \ c_{L}^{y} \ c_{R} \ + H \ c.];}$$
 (10)

$$H_{V} = V \prod_{n_{L}}^{X} n_{R} \circ$$
 (11)

where c_i annihilates an electron of pseudo-spin in dot i. A spin-dependent tunneling term t and a tunneling term with spin ip s emerge, which are dened by t = C $^{(0)2}$ t₁₁ + C $^{(1)L}$ C $^{(1)R}$ t₂₂ + 2C $^{(2)}$ t₁₃;s = (C $^{(1)L}$ + C $^{(1)R}$)t₁₂; where t_{nm} represents the tunneling amplitude from leveln in dot L to levelm in dot R. The relevant lowest four eigenenergies and their eigenfunctions are obtained by the elective exchange H amiltonian using local spin operators:

$$H_{EX} = J_k S_{Lz} S_{Rz} + J_? (S_{Lx} S_{Rx} + S_{Ly} S_{Ry}) + u_z (S_{Lz} + S_{Rz});$$
 (12)

where $J_k = \frac{2\left(t_n^2+t_k^2\right)}{U-V} - \frac{4s^2\left(U-V\right)}{\left(U-V\right)^2-\frac{u^2}{u^2}}; J_? = \frac{4t_nt_k}{U-V},$ and $\mathbf{u}_z = \mathbf{u}_z \left(1 - \frac{2s^2}{\left(U-V\right)^2-\frac{u^2}{u^2}}\right)$ with $s = \frac{1}{2}\left(s_n + \frac{M}{N}\frac{R_{12}}{L_{12}}s_\sharp\right)$. It is well known that the SO interaction makes the exchange Ham iltonian anisotropic [27]. In contrast to the SO case, where the anti-sym metric term dominates, the dominant anisotropic correction of H $_{E,X}$ in a slanting eld is the sym metric term. Nevertheless, C-NOT operation can be accomplished by this anisotropic exchange Ham iltonian simply by replacing J of the Heisenberg Ham iltonian by J_k , and single-qubit operation (SESR) with replacing \mathbf{u}_{0z} by \mathbf{u}_z , as is shown in Refs: [26, 27].

In conclusion, we propose a viable qubit based on combining the orbital and spin degrees of freedom of an electron in a QD placed in a slanting Zeem an eld. Both single-qubit rotation and the C-NOT operation are demonstrated. This qubit is easier to manipulate than a spin qubit and has a better quality factor than a charge qubit. The concept is general and can be applied to a range of systems such as single wall carbon nanotubes, GaAs, and SiGeQDs. This scheme also allows for the measurement of the intrinsic single electron spin coherence time.

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